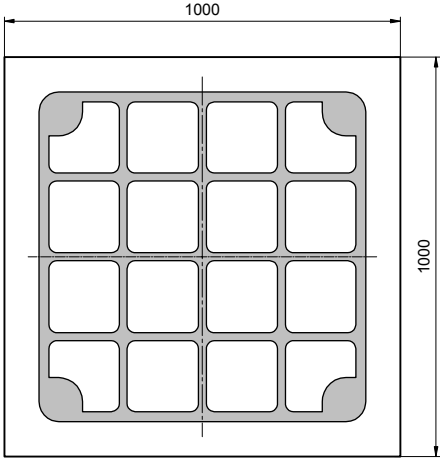


Radiation	Type	Technology	Electrodes
Red-orange	solderable	AllnGaP/GaAs	P (anode) up

 <p>PoC-05</p>	typ. dimensions (μm)
	<u>typ. thickness</u> 260 (± 20) μm <u>cathode</u> gold alloy, 1.5 μm <u>anode</u> gold alloy, 1.5 μm

Optical and Electrical Characteristics

$T_{\text{amb}} = 25^{\circ}\text{C}$, unless otherwise specified

Parameter	Test conditions	Symbol	Min	Typ	Max	Unit
Forward voltage	$I_F = 100 \text{ mA}$	V_F		1.9	2.3	V
Forward voltage	$I_F = 300 \text{ mA}$	V_F		2.1		V
Reverse voltage	$I_F = 10 \mu\text{A}$	V_R	5			V
Radiant power ¹	$I_F = 100 \text{ mA}$	Φ_e	4.6	6.0		mW
Radiant power ¹	$I_F = 300 \text{ mA}$	Φ_e		16		mW
Luminous intensity ¹	$I_F = 100 \text{ mA}$	I_V	225	290		mcd
Peak wavelength	$I_F = 100 \text{ mA}$	λ_p	635	645	655	nm
Spectral bandwidth at 50%	$I_F = 100 \text{ mA}$	$\Delta\lambda_{0.5}$		16		nm
Switching time	$I_F = 100 \text{ mA}$	t_r, t_f		40		ns

¹Measured on bare chip on TO-18 header with *EPIGAP* equipment

Labeling

Type	Lot N°	$\Phi_e(\text{typ})$ [mW]	$V_F(\text{typ})$ [V]	Quantity
ELC-645-11-05				

Packing: Chips on adhesive film with wire-bond side on top